

Gunter Semiconductor GmbH

GFC110

N Channel Power MOSFET with low $R_{DS(on)}$

Chip Specification

General Description:

- * Advanced Process Technology
- * Dynamic dV/dt Rating
- * **175°C Operating Temperature**
- * **Fast Switching**
- * **Fully Avalanche Rated**
- * **Low $R_{DS(on)}$**

Mechanical Data:

D3

Dimension **1.61mm x 2.21mm**

Thickness: **400 μm**

Metallization:

Top : : **Al**

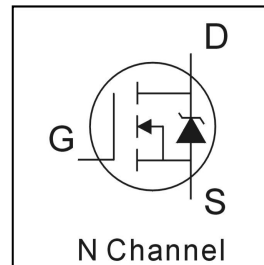
Backside : **CrNiAg / Au**

Suggested Bonding Conditions:

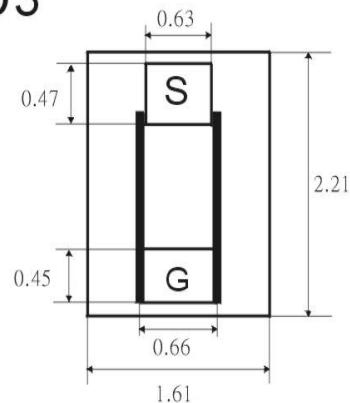
Die Mounting: **Solder Perform**

95/5 PbSn or 92.5/2.5/5 PbAgIn

Source Bonding Wire: **5 mil Al**



D3



100V, N Channel

Absolute Maximum Rating

@ $T_a=25^{\circ}\text{C}$

Characteristics	Symbol	Limit	Unit	Test Conditions
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	100	V	$V_{GS}=0V$, $I_D=250\mu A$
Static Drain-to - Source On-resistance	$R_{DS(ON)}$	0.54	Ω	$V_{GS}=10V$, $I_D=3.4A$
Continuous Drain current (in target package)	$I_{D@25^{\circ}\text{C}}$	5.6	A	$V_{GS}=10V$
Continuous Drain current (in target package)	$I_{D@100^{\circ}\text{C}}$	4	A	$V_{GS}=10V$
Operation Junction	T_j	-55~175	$^{\circ}\text{C}$	
Storage Temperature	T_{STR}	-55~175	$^{\circ}\text{C}$	

Target Device: IRF510

TO-220AB

P_D

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W

@ $T_c=25^{\circ}\text{C}$